

# TLS Kondo effect in structurally disordered ThAsSe

T. Cichorek<sup>a,b,\*</sup>, Z. Henkie<sup>b</sup>, J. Custers<sup>a</sup>, P. Gegenwart<sup>a</sup>, F. Steglich<sup>a</sup>

<sup>a</sup>Max Planck Institute for Chemical Physics of Solids, Dresden D-01187, Germany

<sup>b</sup>Institute of Low Temperature and Structure Research, Polish Academy of Sciences, 50-950 Wrocław, Poland

## Abstract

Low-temperature electrical-resistivity,  $\rho(T)$ , measurements on single crystals of the structurally disordered ThAsSe reveal an anomalous scattering mechanism, which is apparently derived from two-level systems. For the ThAsSe specimen displaying a resistivity saturation at millikelvin temperatures, a crossover from a logarithmic to a non-Fermi-liquid behavior  $\Delta\rho \propto 1 - aT^{1/2}$  is observed upon cooling below  $\simeq 4$  K. A comparison of experimental results with the theoretical ones yields a characteristic energy scale of the order of a few K for ThAsSe.

Non-magnetic interaction of a degenerate Fermi gas with structural two-level systems (TLS) may cause a logarithmic correction to  $\rho(T)$ , i.e., a behavior analogous to the spin Kondo effect [1]. Even more remarkable is a realization of a two-channel Kondo effect, as predicted when the Kondo temperature,  $T_K$ , exceeds the energy splitting between the localized states,  $\Delta_{\text{TLS}}$ . A temperature variation of the additional resistivity due to the TLS–electron interaction,  $\rho_{\text{TLS}}$ , is shown in the inset of Fig. 1 in a schematic way: Upon cooling below  $T_K$ , the  $-\log T$  dependence transforms into the non-Fermi liquid (nFL) behavior  $\rho_{\text{TLS}} \propto 1 - aT^{1/2}$ . At the lowest temperatures,  $\rho_{\text{TLS}}$  saturates and the Fermi-liquid state eventually develops [1].

Recently, we have reported an anomalous scattering mechanism in the structurally disordered ThAsSe [2]. At  $T \lesssim 20$  K, its  $\rho(T)$  displays a  $-\log T$  correction that holds over one decade in temperature and is unaffected by neither magnetic fields up to 13.5 T (cf. the inset of Fig. 2) nor hydrostatic pressures as high as 1.88 GPa [3]. Additionally, for various single crystals a saturation of

$\rho(T)$  between 0.2 and 2 K was observed [2]. Most probably, the low-lying excitations of the electron gas in ThAsSe are due to the TLS–electron interaction. Dynamic disorder in this diamagnet was reflected by a quasilinear-in- $T$  term of non-electronic origin in the specific heat at  $T \lesssim 1.7$  K [2].

An example of a complex  $\rho(T)$  behavior in ThAsSe, presented as the  $\Delta\rho(T)/\rho(0.05 \text{ K})$  data on a semi-logarithmic temperature scale, is given in Fig. 1. Following observations are made below 20 K: (i) At higher temperatures,  $\rho(T)$  logarithmically increases with lowering temperature down to  $T^*$ . A rough approximation for  $T^*$  yields a value somewhat larger than 2 K. (ii) Upon further cooling,  $\rho(T)$  significantly deviates from the  $-\log T$  dependence. (iii) An increase of  $\rho(T)$  holds down to  $T_S \simeq 0.2$  K, at which the saturation sets in.

In order to determine a temperature variation of the electrical resistivity at  $T_S < T < T^*$ , we re-plotted our data on a  $T^{1/2}$  scale. The results are depicted in Fig. 2, where the value of  $\rho_{ab}(300 \text{ K}) = 220 \mu\Omega \text{ cm}$  was taken from Ref. [4]. As indicated by the solid line, a  $T^{1/2}$  dependence holds between around  $\sim 0.2$  and 6 K. The latter value is larger than  $T^* = 2$  K, as estimated from Fig. 1. We emphasize that an unambiguous approximation of  $T^*$  cannot be expected in real, macroscopic samples where there are many TLS centers [1].

\*Corresponding author. Max Planck Institute for Chemical Physics of Solids, Noethnizer Str. 40, Dresden D-01187, Germany. Tel.: +49-351-4646-3133; fax: +49-351-4646-3119.

E-mail address: cichorek@cpfs.mpg.de (T. Cichorek).

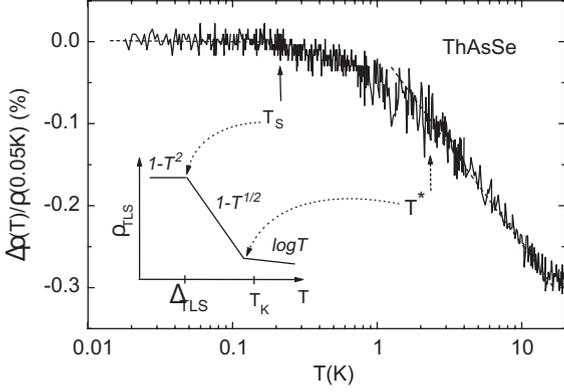


Fig. 1. The *ab*-plane resistivity normalized to the corresponding value at 0.05 K,  $\Delta\rho(T)/\rho(0.05\text{ K})$ , for the ThAsSe single crystal. The solid arrow at  $T_S$  marks the temperature of saturation. The dashed arrow indicates the temperature,  $T^*$ , below which  $\rho(T)$  deviates from a  $-\log T$  dependence. Dashed lines are a guide to the eye only. Inset: Expected temperature dependence of  $\rho_{\text{TLS}}$  shown in a schematic way for the case of  $\Delta_{\text{TLS}} \ll T_K$ .

As mentioned above, the anomalous low- $T$  properties of ThAsSe are apparently caused by the TLS–electron interaction. Furthermore, the ThAsSe sample with  $T_S \approx 0.2$  K displays a far-reaching similarity of the experimental  $\rho(T)$  results to the theoretical ones. Therefore, for this particular specimen, we roughly estimate a characteristic energy scale in terms of the TLS Kondo model: Firstly, we consider  $T_S \approx 0.2$  K as the temperature of the breakdown of the nFL scaling  $\Delta\rho \propto T^{1/2}$ . Further, we take  $T_K = 5$  K, i.e., slightly more than an average value of  $T^* \approx 4$  K inferred from Figs. 1 and 2. Note that  $T^*$  represents a low-temperature limit of the  $-\log T$  dependence that is expected to hold at  $T_K < T$ . Finally, we get a crude estimate of the energy splitting  $\Delta_{\text{TLS}} \approx (T_K T_S)^{1/2} \approx 1$  K. Thus, the  $\Delta_{\text{TLS}} \ll T_K$  requirement for the two-channel Kondo effect seems to be fulfilled in the ThAsSe sample discussed. Nevertheless, the large value of the Kondo temperature remains unclear, although the recent theoretical studies have shown that  $T_K$  of the order of 0.5 K can be

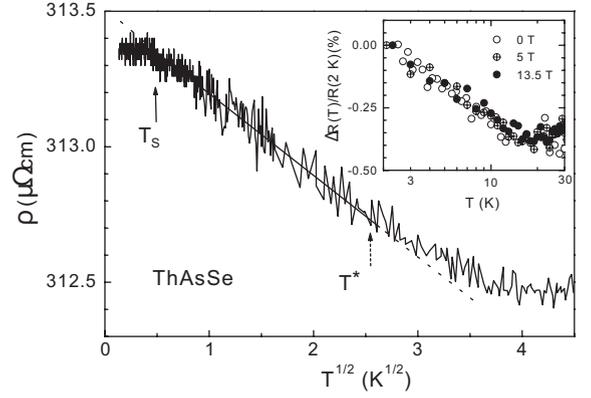


Fig. 2. The *ab*-plane resistivity of the structurally disordered ThAsSe showing a  $T^{1/2}$  behavior in a temperature window  $T_S < T < T^*$ , as indicated by the solid line. Inset: The low- $T$  upturn for another single crystal of ThAsSe shown on a semi-logarithmic temperature scale. The results, plotted as  $\Delta\rho(T)/\rho(2\text{ K})$ , were obtained along the *ab*-plane in varying magnetic fields applied along the *c*-axis.

achieved outside the tunneling regime, i.e., when the first excited state is above the barrier [5].

To conclude, a complex low- $T$  behavior of  $\rho(T)$  in the structurally disordered ThAsSe was observed. Though the enhanced energy scale, our  $\rho(T)$  results appear to be consistently interpreted in terms of the TLS Kondo model. In particular, indications towards a two-channel Kondo effect and the resultant nFL properties  $\Delta\rho \propto 1 - aT^{1/2}$  derived from structural two-level systems were found for the ThAsSe single crystal with the very small value of  $T_S \approx 0.2$  K.

## References

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